

AMENDMENTS TO CLAIMS

- Please amend pending claims 11 and 15 as indicated below.
- Please add new claims 19-22.

A complete listing of all claims and their status in the application are as follows:

Claims 1-10 (canceled)

11. (currently amended) An integrated circuit comprising:
a semiconductor substrate having a semiconductor device provided thereon;
a dielectric layer ~~of further comprising a~~ non-barrier dielectric material capable of
being changed into a barrier dielectric material and having a opening provided
therein, the dielectric layer around the opening of the barrier dielectric material
which separates the non-barrier dielectric material from the opening; and
a conductor core over the dielectric layer to fill the opening and connect to the
semiconductor device.

12. (original) The integrated circuit as claimed in claim 11 wherein the
dielectric layer is of SiCOH as the non-barrier dielectric material.

13. (original) The integrated circuit as claimed in claim 11 wherein the
dielectric layer is of SiCOH as the non-barrier dielectric material and the dielectric layer is of
SiC(H) as the barrier dielectric material.

14. (original) The integrated circuit as claimed in claim 11 wherein the
conductor core is of a material from a group consisting of copper, aluminum, gold, silver, a
compound thereof, and a combination thereof.

15. (currently amended) An integrated circuit comprising:
a semiconductor substrate having a semiconductor device provided thereon;
a dielectric layer ~~of further comprising a~~ non-barrier dielectric material capable of
being reduced into a barrier dielectric material and having a opening provided
therein, the dielectric layer around the opening of the barrier dielectric material
which separates the non-barrier dielectric material from the opening;
a seed layer over the dielectric layer to line the opening;

a conductor core over the seed layer to fill the opening and connect to the semiconductor device; and
planarizing the conductor core and the seed layer to form a channel.

16. (previously presented) The integrated circuit as claimed in claim 15 wherein the dielectric layer is of SiCOH as the non-barrier dielectric material.

17. (previously presented) The integrated circuit as claimed in claim 15 wherein the dielectric layer is of SiCOH as the non-barrier dielectric material and the dielectric layer is of SiC(H) as the barrier dielectric material.

18. (previously presented) The integrated circuit as claimed in claim 15 wherein the seed layer and the conductor core are of a material from a group consisting of copper, aluminum, gold, silver, a compound thereof, and a combination thereof.

19. (new) The integrated circuit as claimed in claim 11 further comprising a gettering material on the barrier dielectric material.

20. (new) The integrated circuit as claimed in claim 11 further comprising a gettering material of an atomic layer thickness on the barrier dielectric material.

21. (new) The integrated circuit as claimed in claim 15 further comprising an oxygen getting material on the barrier dielectric material.

22. (new) The integrated circuit as claimed in claim 15 further comprising an oxygen getting material of an atomic layer thickness on the barrier dielectric material.